

Amendments to the Specification:

Replace the paragraph starting at page 9, line 2, of the original specification with the following paragraph.

The lower plate 18 is formed to have a plurality of through holes having required diameters across the entire surface of the plate as explained earlier. These through holes 18a pass the radicals generated by the plasma produced in the plasma generation chamber 21 and allow them to diffuse into the film deposition chamber 13. These through holes 18a are set with diameters so that only the radicals can pass through them. Silicon-based material gas (for example, SiH_4) is supplied from a material gas feeder 32 provided with a valve 31 to the lower plate 18. The material gas is introduced into the reserve space 51 formed in the lower plate 18. Next, it is introduced into the film deposition chamber 13 through the plurality of diffusion holes 33.